
2SA844

Silicon PNP Epitaxial

HITACHI

Application

Low frequency amplifier

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA844

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|------------------------------|-----------|-------------|------|
| Collector to base voltage | V_{CBO} | -55 | V |
| Collector to emitter voltage | V_{CEO} | -55 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Collector current | I_C | -100 | mA |
| Emitter current | I_E | 100 | mA |
| Collector power dissipation | P_C | 300 | mW |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

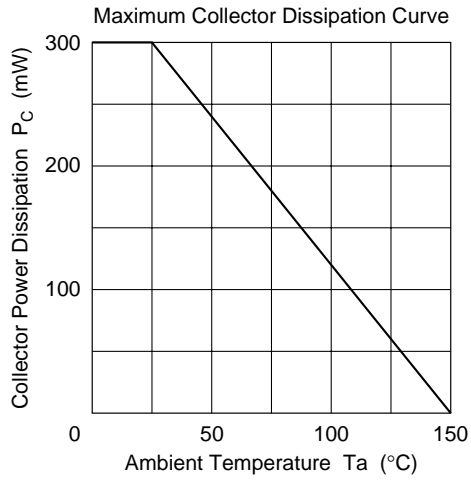
Electrical Characteristics (Ta = 25°C)

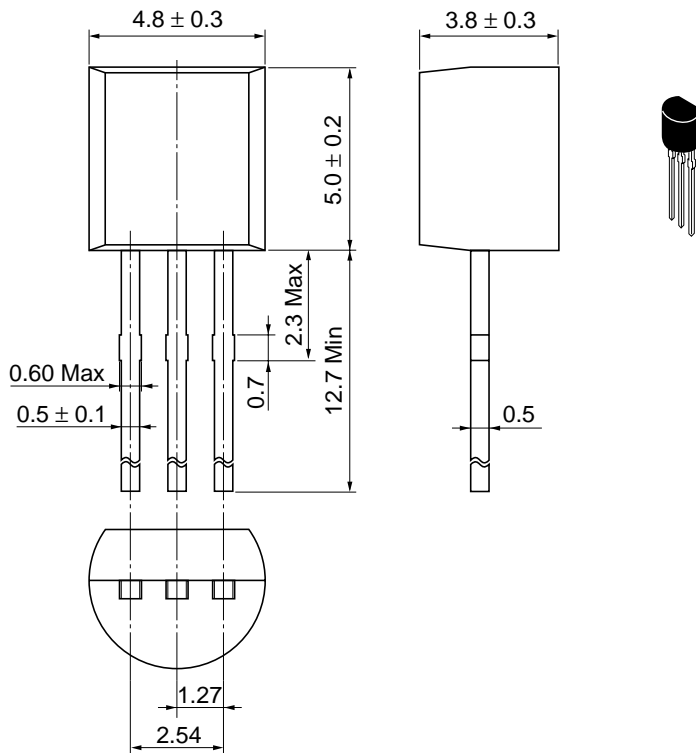
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|---------------|-----|-------|-------|------|--|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | -55 | — | — | V | $I_C = -10 \mu A, I_E = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | -55 | — | — | V | $I_C = -1 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | -5 | — | — | V | $I_E = -10 \mu A, I_C = 0$ |
| Collector cutoff current | I_{CBO} | — | — | -100 | nA | $V_{CB} = -18 \text{ V}, I_E = 0$ |
| Emitter cutoff current | I_{EBO} | — | — | -50 | nA | $V_{EB} = -2 \text{ V}, I_C = 0$ |
| DC current transfer ratio | h_{FE}^{*1} | 160 | — | 800 | | $V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | — | -0.1 | -0.5 | V | $I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$ |
| Base to emitter voltage | V_{BE} | — | -0.66 | -0.75 | V | $V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$ |
| Gain bandwidth product | f_T | — | 200 | — | MHz | $V_{CE} = -12 \text{ V}, I_E = -2 \text{ mA}$ |
| Collector output capacitance | C_{ob} | — | 2.0 | — | pF | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ |

Note: 1. The 2SA844 is grouped by h_{FE} as follows.

| C | D | E |
|------------|------------|------------|
| 160 to 320 | 250 to 500 | 400 to 800 |

See characteristic curves of 2SA836.





| | |
|--------------------------|-----------|
| Hitachi Code | TO-92 (1) |
| JEDEC | Conforms |
| EIAJ | Conforms |
| Weight (reference value) | 0.25 g |

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